

# BRCS3134WA

Rev.D Feb.-2024

## / Descriptions

SOT-323 N MOS

N-Channel MOSFET in a SOT-323 Plastic Package.

## / Features

2KV

Sensitive gate trigger current and Low Holding current.ESD protected up to 2KV, HF Product.

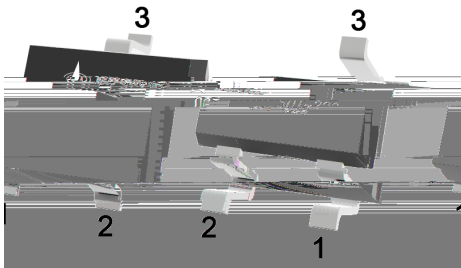
## / Applications

Intended for use in general purpose switching and phase control applications.

## / Equivalent Circuit



## / Pinning



Pin1:G Pin2:S Pin3:D

## / Marking

See Marking Instructions.

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DATA SHEET

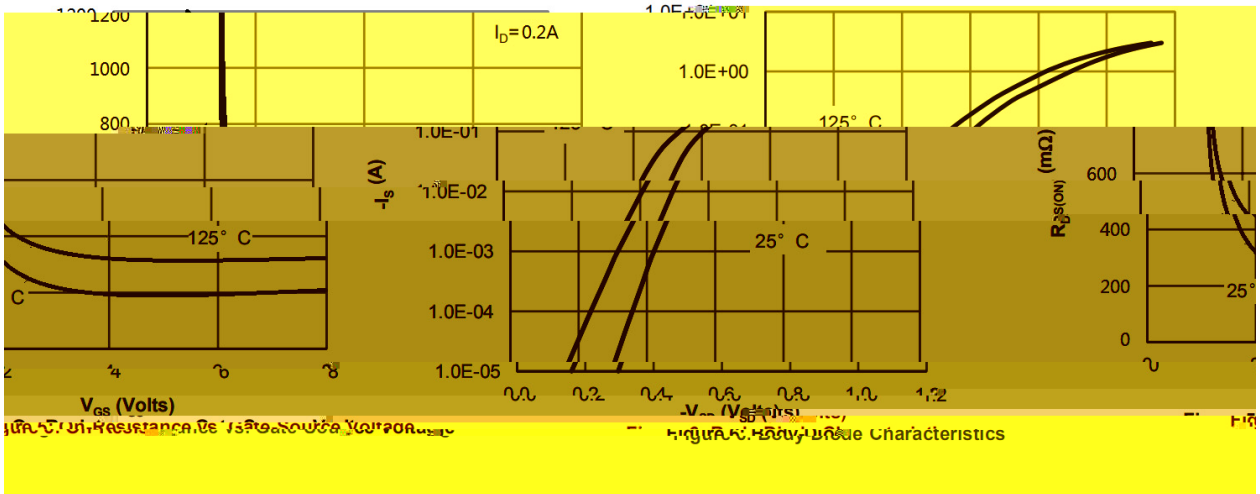
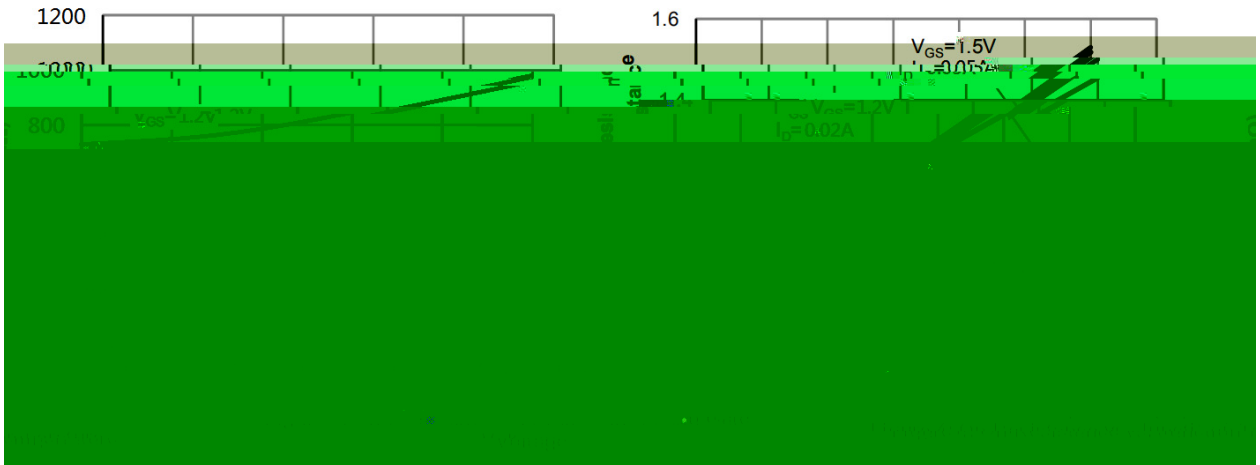
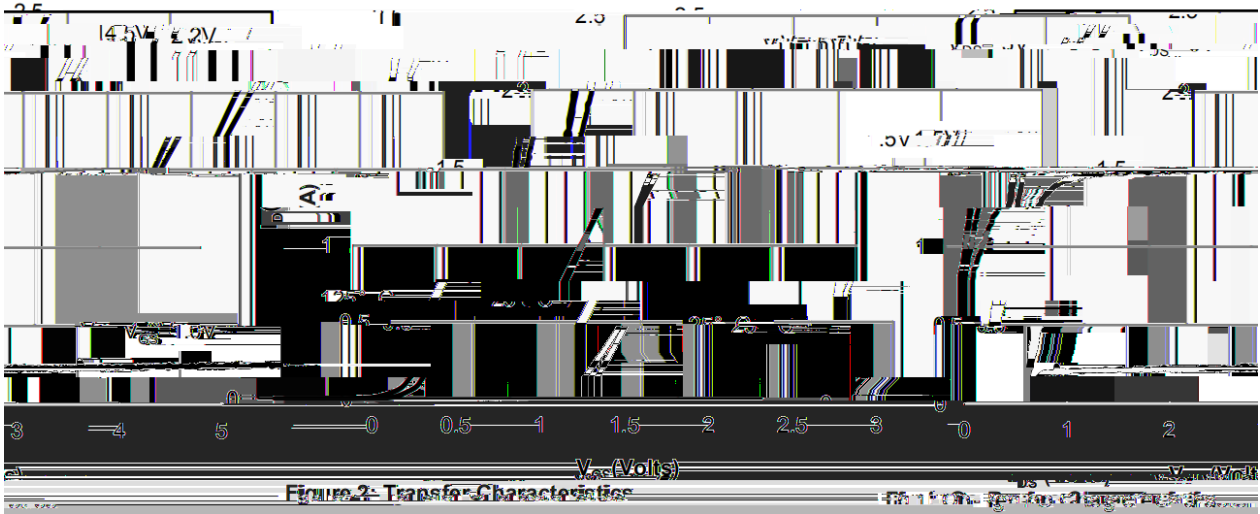
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DSS}$	20	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V	
Drain Current – Continuous	$I_D$	0.75	A	
Pulsed Drain Current	$I_{DM}$	3	A	
Power Dissipation	$P_D$	200	mW	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		
Thermal resistance, junction - ambient	t 10s	$R_{JA}$	450	/W
	Steady-State		570	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{DSS}$	$V_{GS}=0$ $I_D=250\mu A$	20	22.9		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0$ $V_{DS}=20V$			1	A

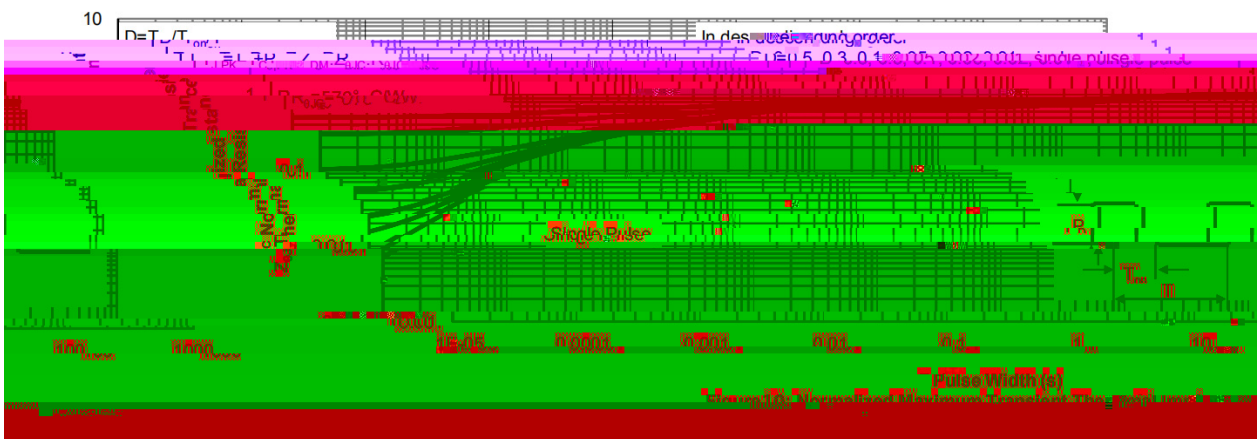
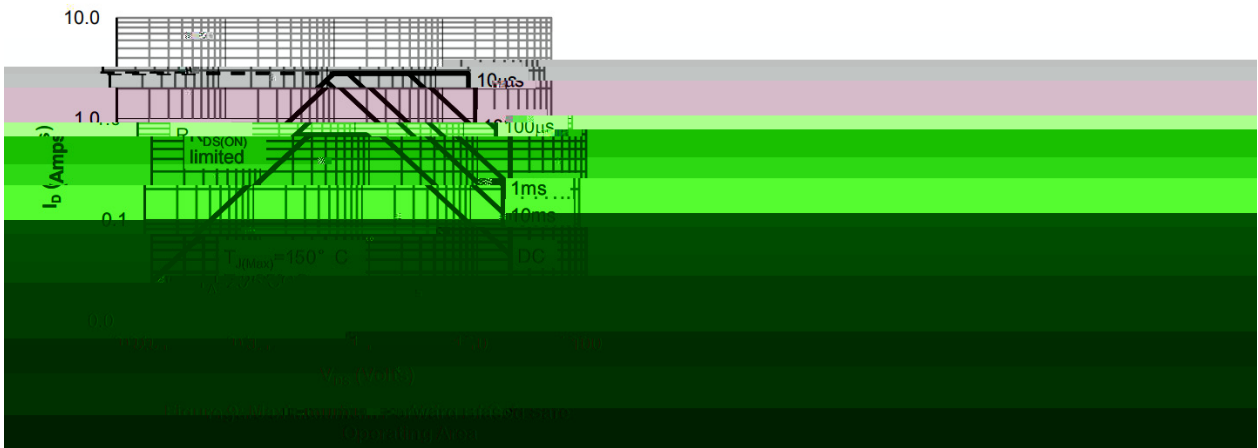
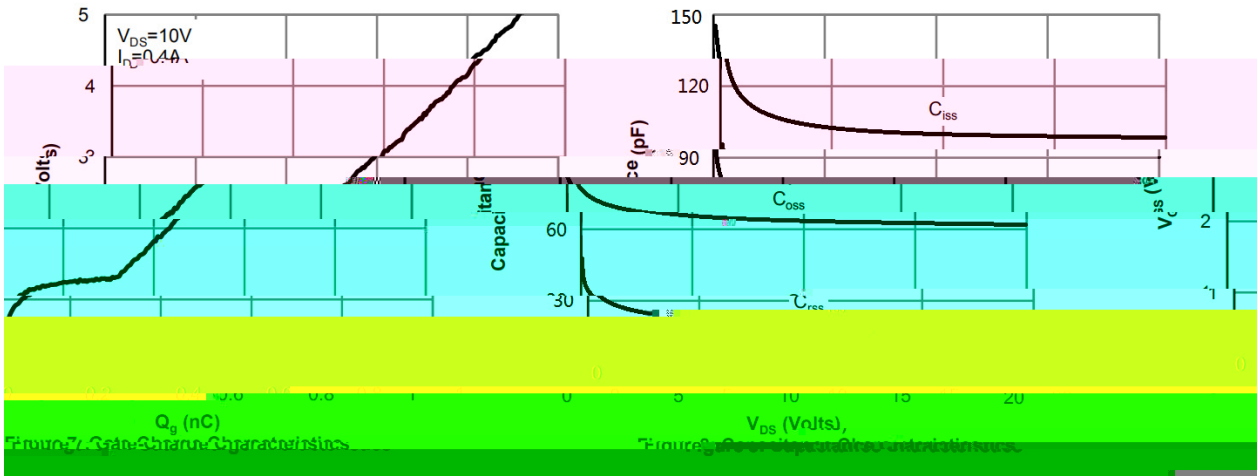
## / Electrical Characteristics(Ta=25 )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_g$	$V_{GS}=4.5V,$ $I_D=0.4A$ $V_{DS}=10V,$		0.85		nC
Gate Source Charge	$Q_{gs}$			0.1		
Gate Drain Charge	$Q_{gd}$			0.25		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=4.5V$ $R_L=25$ $V_{DS}=10V$ $R_{GEN}=3$		2		ns
Turn-On Rise Time	$t_r$			4		ns
Turn-Off Delay Time	$t_{d(off)}$			18		ns
Turn-Off Fall Time	$t_f$			8		ns

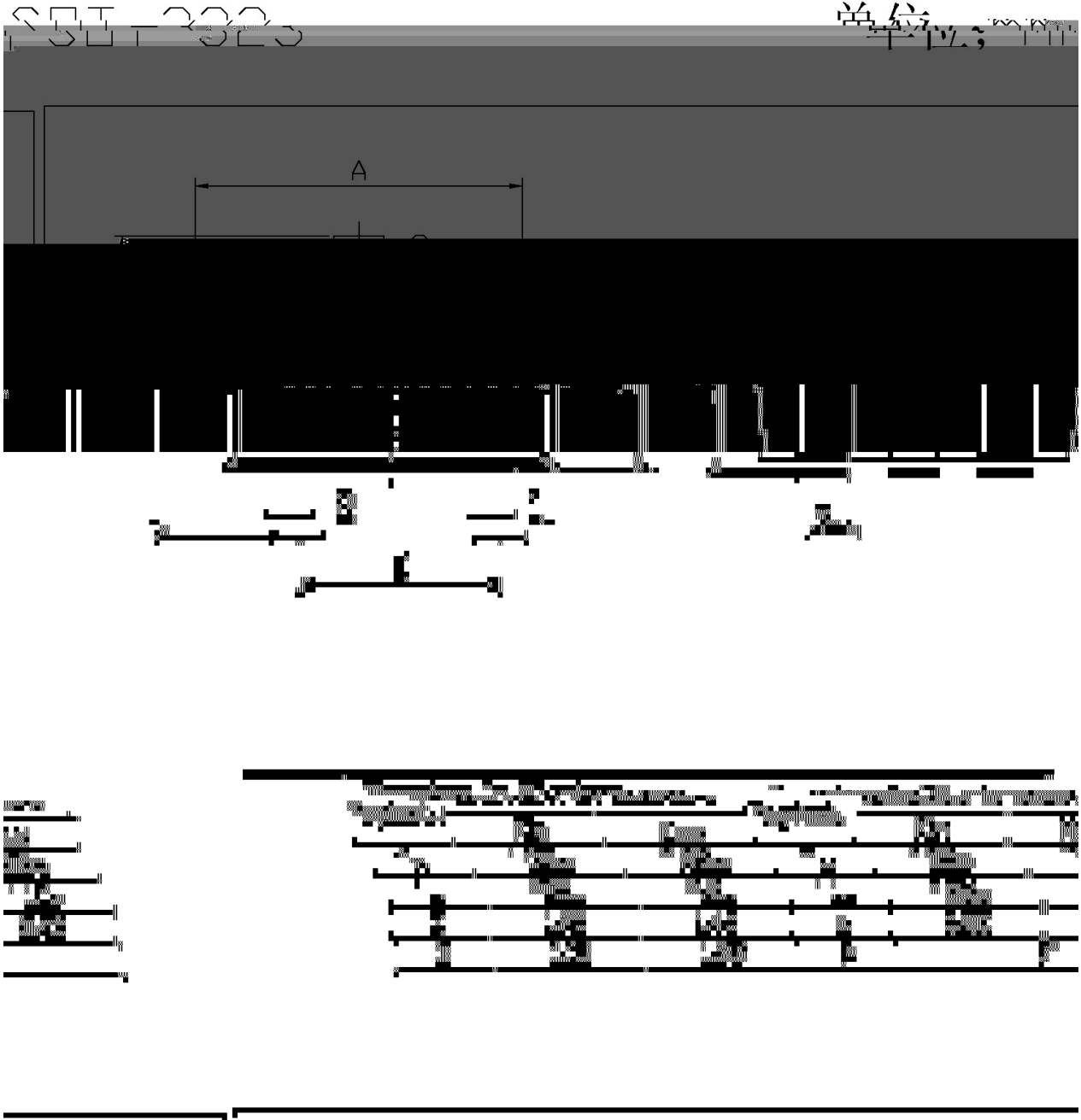
/ Electrical Characteristic Curve



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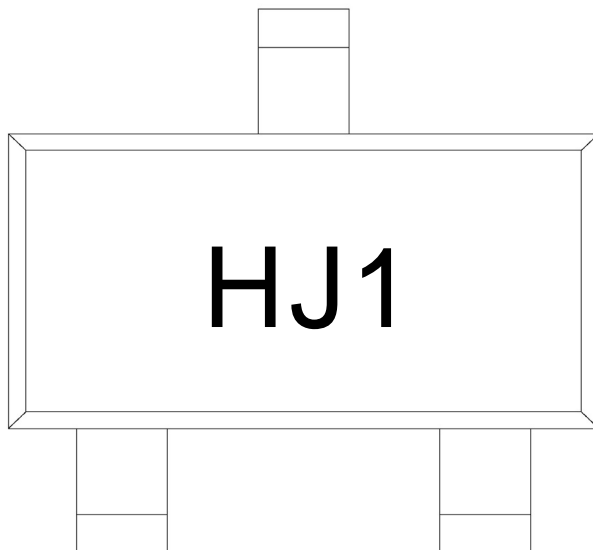


/ Package Dimensions





**/ Marking Instructions**



H

J1

Note:

H: Company Code

J1: Product Type Code

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